

RJK4532DPH-E0

450V - 4A - MOS FET
High Speed Power Switching

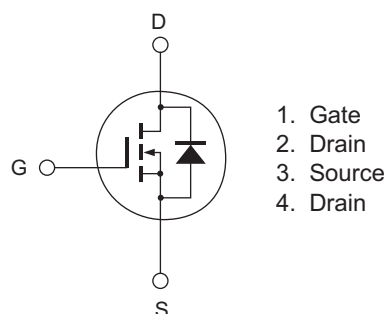
R07DS1038EJ0100
Rev.1.00
Mar 15, 2013

Features

- Low on-state resistance
 $R_{DS(on)} = 1.9 \Omega$ typ. (at $I_D = 2.0 \text{ A}$, $V_{GS} = 10 \text{ V}$, $T_a = 25^\circ\text{C}$)
- Low drive current
- High speed switching

Outline

RENESAS Package code: PRSS0004ZJ-B
(Package name: TO-251)



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	450	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	4	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	16	A
Body-drain diode reverse drain current	I_{DR}	4	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	16	A
Avalanche current	I_{AP} ^{Note3}	3	A
Avalanche energy	E_{AR} ^{Note3}	0.5	mJ
Channel dissipation	P_{ch} ^{Note 2}	40.3	W
Channel to case thermal Impedance	θ_{ch-c}	3.1	$^\circ\text{C/W}$
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. Pulse width limited by safe operating area.

2. Value at $T_c = 25^\circ\text{C}$

3. $ST_{ch} = 25^\circ\text{C}$, $T_{ch} \leq 150^\circ\text{C}$

Electrical Characteristics

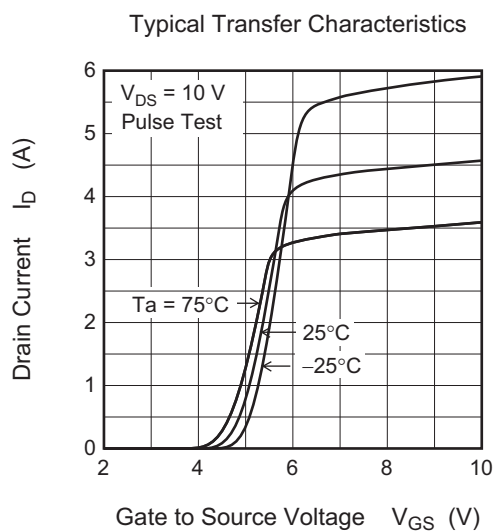
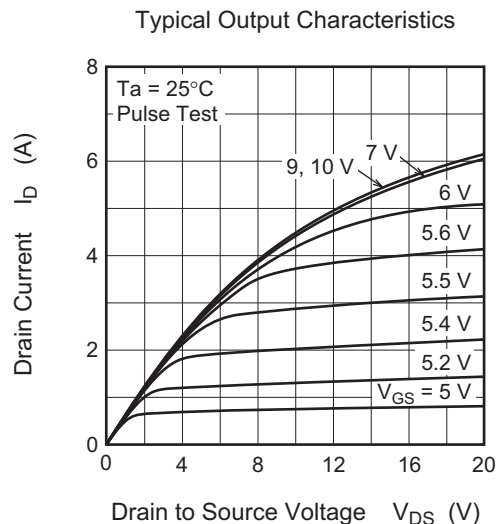
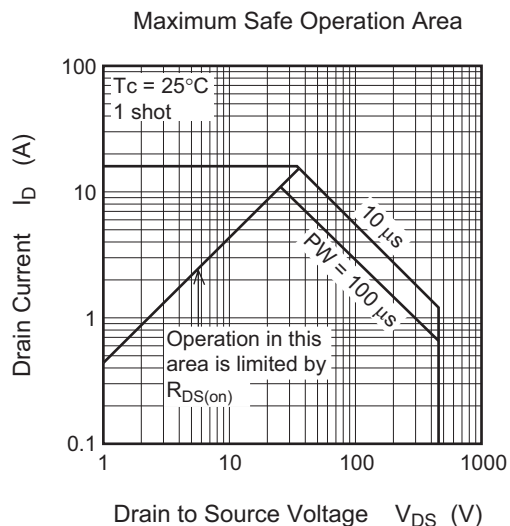
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	450	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 450 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	—	4.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.9	2.3	Ω	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 4}
Input capacitance	C_{iss}	—	280	—	pF	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	36	—	pF	
Reverse transfer capacitance	C_{rss}	—	4	—	pF	
Turn-on delay time	$t_{d(on)}$	—	9.0	—	ns	$I_D = 2 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 113 \Omega$ $R_g = 10 \Omega$
Rise time	t_r	—	4.5	—	ns	
Turn-off delay time	$t_{d(off)}$	—	20.0	—	ns	
Fall time	t_f	—	5.0	—	ns	
Total gate charge	Q_g	—	9.0	—	nC	$V_{DD} = 360 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 4 \text{ A}$
Gate to source charge	Q_{gs}	—	2.0	—	nC	
Gate to drain charge	Q_{gd}	—	4.5	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.9	1.5	V	$I_F = 4 \text{ A}$, $V_{GS} = 0$ ^{Note 4}
Body-drain diode reverse recovery time	t_{rr}	—	215	—	ns	$I_F = 4 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

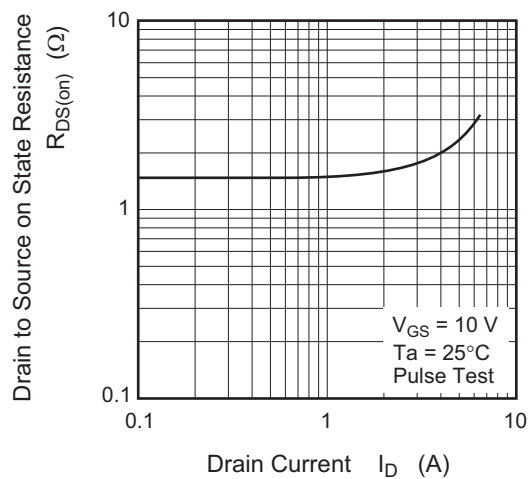
Note: 4. Pulse test

5. Since this device is equipped with high voltage FET chip ($V_{DSS} \geq 600 \text{ V}$), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.
6. This device is sensitive to electrostatic discharge.
It is recommended to adopt appropriate cautions when handling this product.

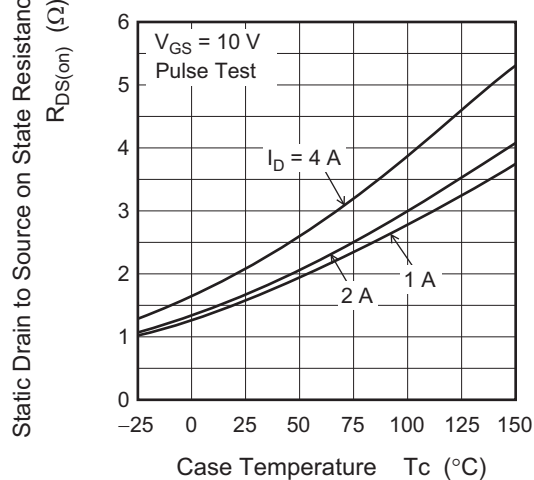
Main Characteristics



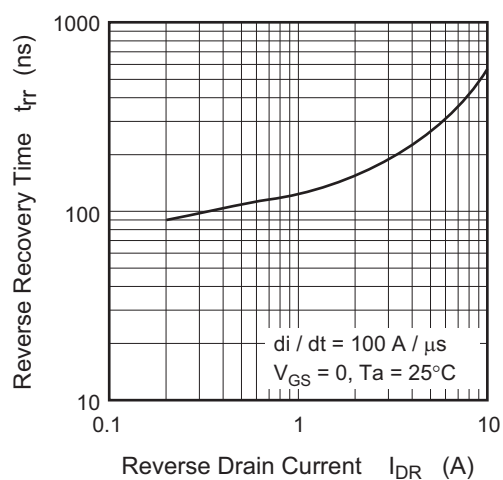
Static Drain to Source on State Resistance vs. Drain Current (Typical)

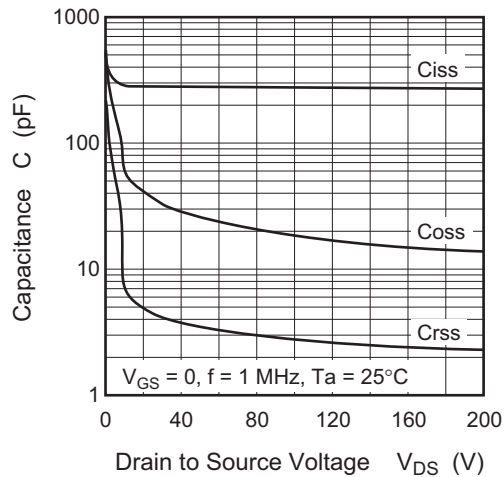


Static Drain to Source on State Resistance vs. Temperature (Typical)

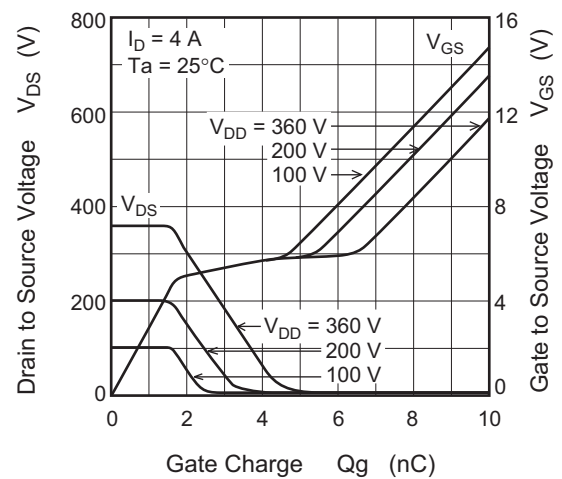
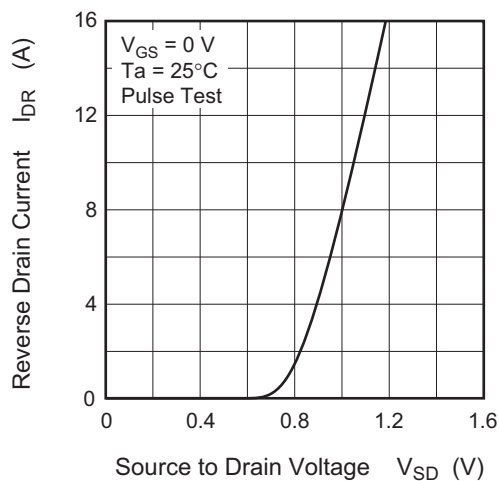
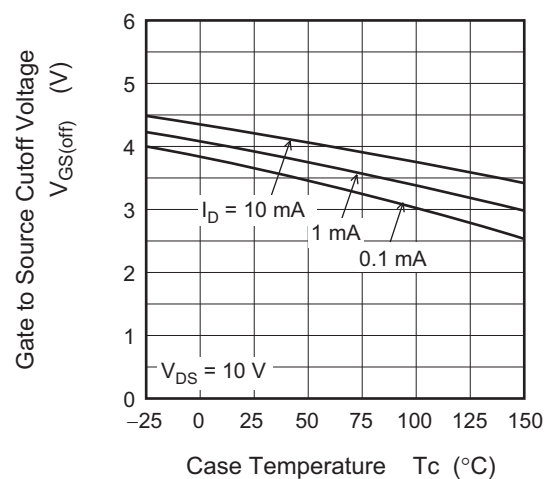


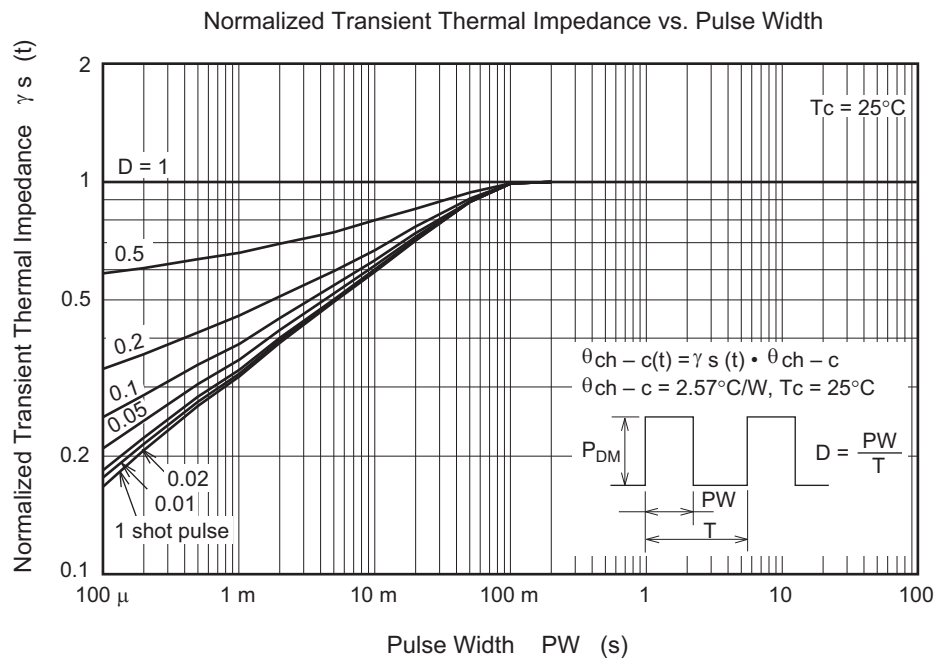
Body-Drain Diode Reverse Recovery Time (Typical)



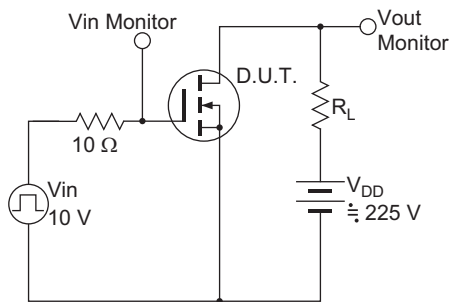
Typical Capacitance vs.
Drain to Source Voltage

Dynamic Input Characteristics (Typical)

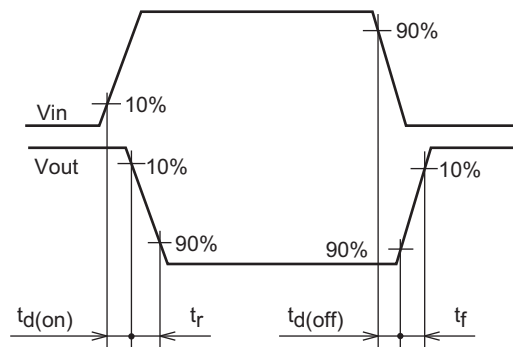
Reverse Drain Current vs.
Source to Drain Voltage (Typical)Gate to Source Cutoff Voltage
vs. Case Temperature (Typical)



Switching Time Test Circuit



Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
TO-251	—	PRSS0004ZJ-B	TO-251S	0.38g	

The drawing shows the mechanical dimensions of the TO-251 package. The top view shows a square body with a width of 6.6 ± 0.5 mm and a height of 6.1 ± 0.5 mm. The distance between the centers of the three leads is 5.34 ± 0.5 mm. The lead height is 0.7 ± 0.5 mm. The lead thickness is 0.96 max. mm. The lead width is 0.76 ± 0.10 mm. The lead length is 1.8 ± 0.5 mm. The total length of the package is 9.3 ± 0.5 mm. The bottom view shows a base with a width of 2.3 mm. The side view shows a height of 2.3 ± 0.5 mm, a width of 0.5 ± 0.5 mm, and a length of 1.02 ± 0.2 mm. The bottom view also shows a width of $0.50^{+0.10}_{-0.05}$ mm.

Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK4532DPH-E0#T2	70 pcs	Tube

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